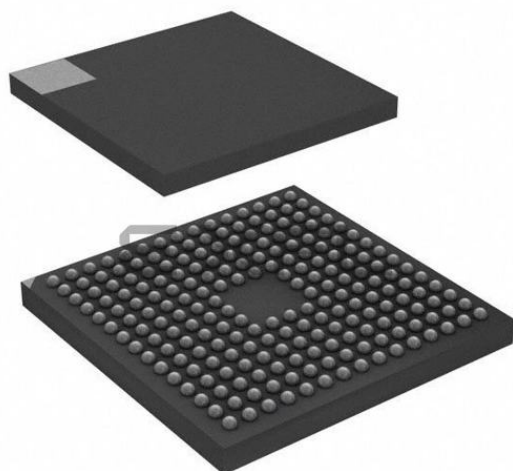




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	168
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	216-TFBGA
Supplier Device Package	216-TFBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f429nih6e

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communicate at speeds of up to 11.25 Mbit/s. The other available interfaces communicate at up to 5.62 bit/s.

USART1, USART2, USART3 and USART6 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller.

Table 8. USART feature comparison⁽¹⁾

USART name	Standard features	Modem (RTS/CTS)	LIN	SPI master	IrDA	Smartcard (ISO 7816)	Max. baud rate in Mbit/s (oversampling by 16)	Max. baud rate in Mbit/s (oversampling by 8)	APB mapping
USART1	X	X	X	X	X	X	5.62	11.25	APB2 (max. 90 MHz)
USART2	X	X	X	X	X	X	2.81	5.62	APB1 (max. 45 MHz)
USART3	X	X	X	X	X	X	2.81	5.62	APB1 (max. 45 MHz)
UART4	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
UART5	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
USART6	X	X	X	X	X	X	5.62	11.25	APB2 (max. 90 MHz)
UART7	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)
UART8	X	-	X	-	X	-	2.81	5.62	APB1 (max. 45 MHz)

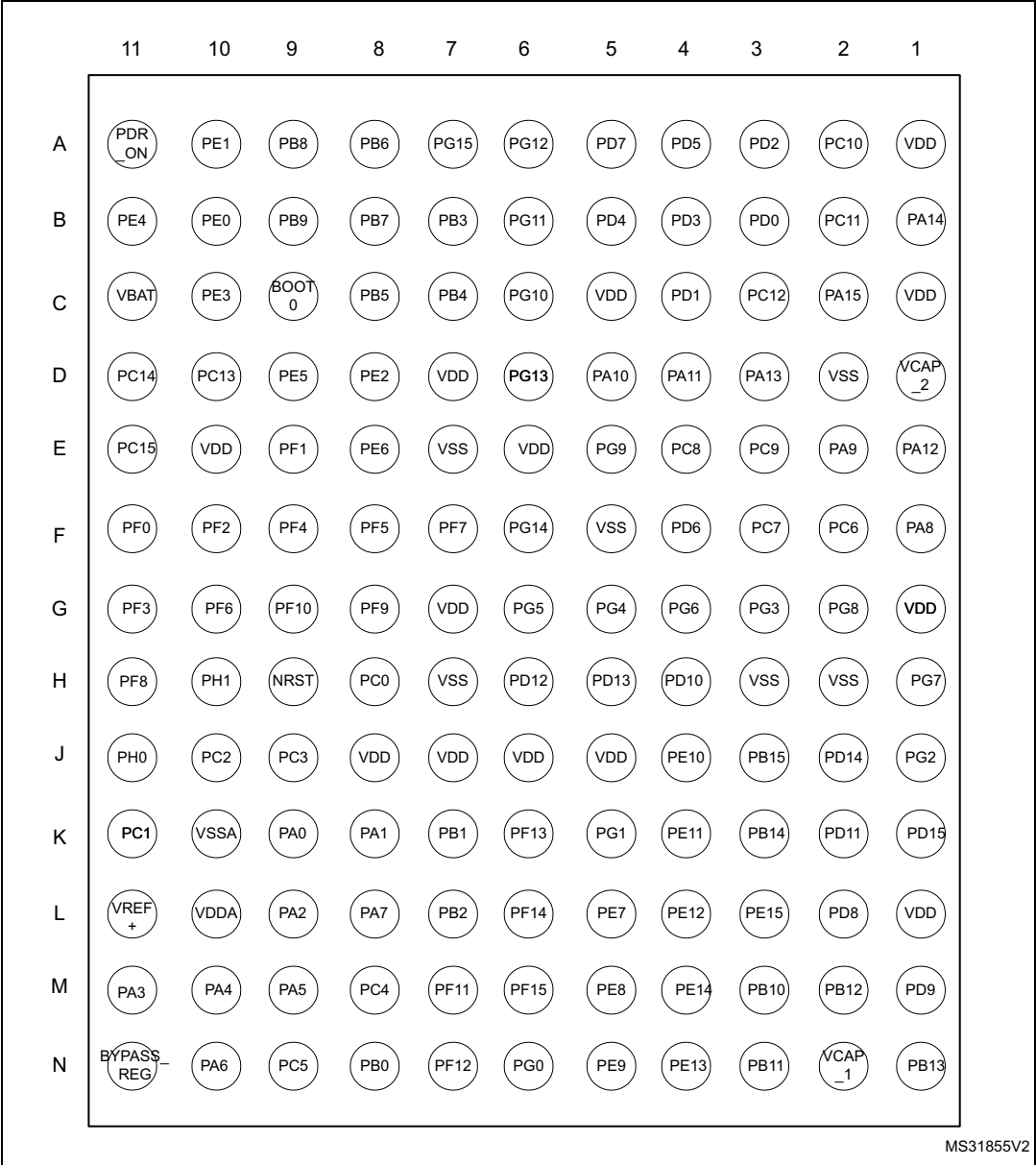
1. X = feature supported.

3.25 Serial peripheral interface (SPI)

The devices feature up to six SPIs in slave and master modes in full-duplex and simplex communication modes. SPI1, SPI4, SPI5, and SPI6 can communicate at up to 45 Mbits/s, SPI2 and SPI3 can communicate at up to 22.5 Mbit/s. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes. All SPIs can be served by the DMA controller.

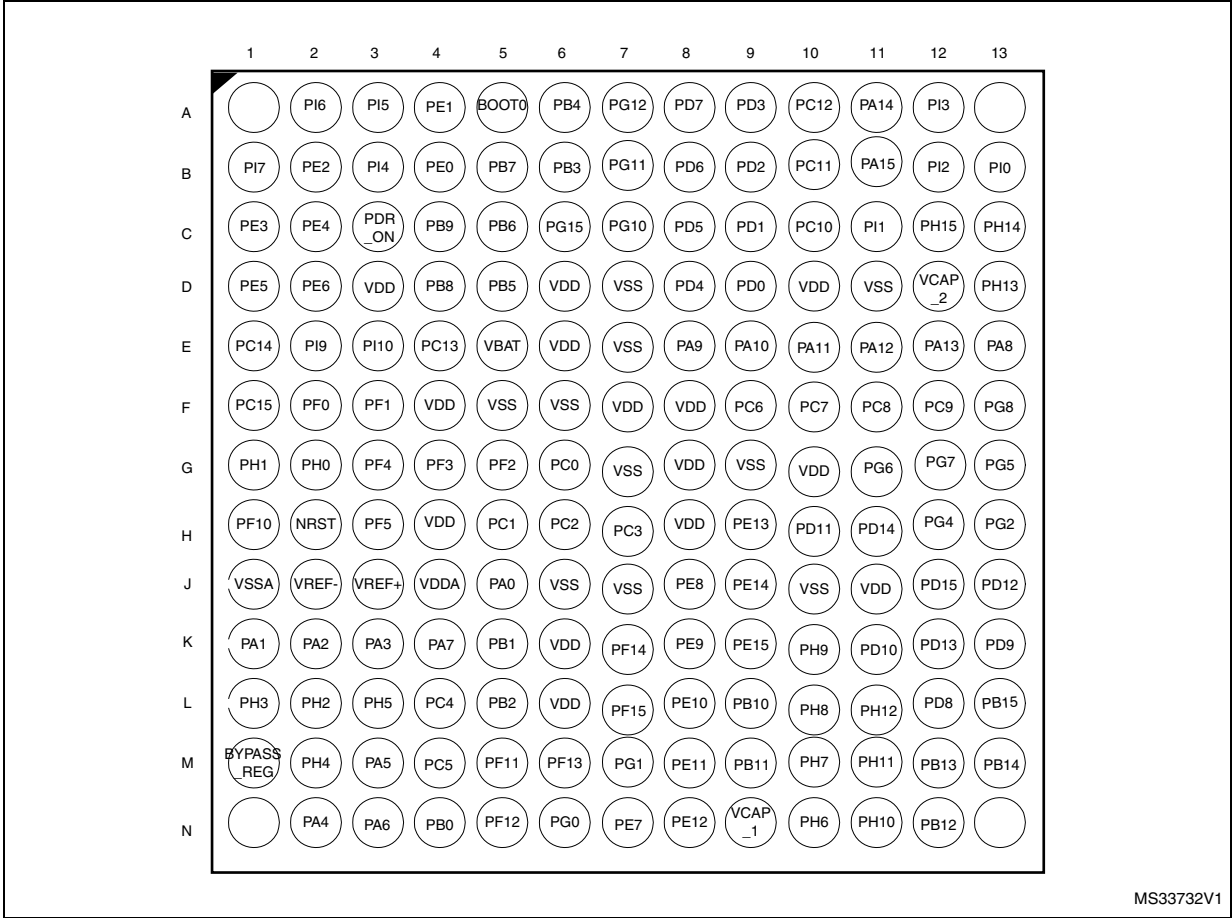
The SPI interface can be configured to operate in TI mode for communications in master mode and slave mode.

Figure 12. STM32F42x WLCSP143 ballout



1. The above figure shows the package bump view.

Figure 16. STM32F42x UFBGA169 ballout



MS33732V1

1. The above figure shows the package top view.
2. The 4 corners balls, A1,A13, N1 and N13, are not bonded internally and should be left not connected on the PCB.

Table 9. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 10. STM32F427xx and STM32F429xx pin and ball definitions

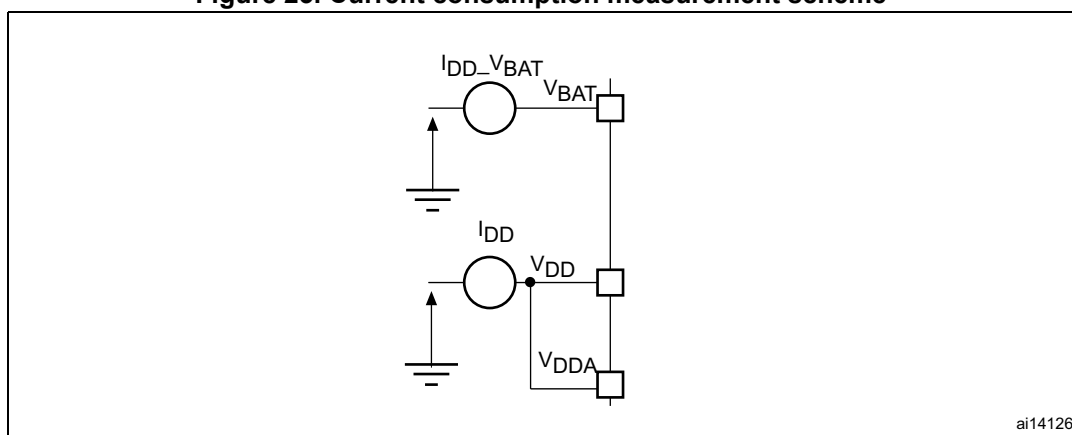
Pin number								Pin name (function after reset) ⁽¹⁾	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
1	1	B2	A2	1	D8	1	A3	PE2	I/O	FT	-	TRACECLK, SPI4_SCK, SAI1_MCLK_A, ETH_MII_TXD3, FMC_A23, EVENTOUT	-
2	2	C1	A1	2	C10	2	A2	PE3	I/O	FT	-	TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	-
3	3	C2	B1	3	B11	3	A1	PE4	I/O	FT	-	TRACED1, SPI4_NSS, SAI1_FS_A, FMC_A20, DCMI_D4, LCD_B0, EVENTOUT	-

Table 12. STM32F427xx and STM32F429xx alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/ 10/11	I2C1/ 2/3	SPI1/2/ 3/4/5/6	SPI2/3/ SAI1	SPI3/ USART1/ 2/3	USART6/ UART4/5/7 /8	CAN1/2/ TIM12/13/14 /LCD	OTG2_HS /OTG1_ FS	ETH	FMC/SDIO /OTG2_FS	DCMI	LCD	SYS
Port A	PA0	-	TIM2_ CH1/TIM2_ ETR	TIM5_ CH1	TIM8_ ETR	-	-	-	USART2_ CTS	UART4_TX	-	-	ETH_MII_ CRS	-	-	-	EVEN TOUT
	PA1	-	TIM2_ CH2	TIM5_ CH2	-	-	-	-	USART2_ RTS	UART4_RX	-	-	ETH_MII_ RX_CLK/E TH_RMII_ REF_CLK	-	-	-	EVEN TOUT
	PA2	-	TIM2_ CH3	TIM5_ CH3	TIM9_ CH1	-	-	-	USART2_ TX	-	-	-	ETH_ MDIO	-	-	-	EVEN TOUT
	PA3	-	TIM2_ CH4	TIM5_ CH4	TIM9_ CH2	-	-	-	USART2_ RX	-	-	OTG_HS_ ULPI_D0	ETH_MII_ COL	-	-	LCD_B5	EVEN TOUT
	PA4	-	-	-	-	-	SPI1_ NSS	SPI3_ NSS/ I2S3_WS	USART2_ CK	-	-	-	-	OTG_HS_ SOF	DCMI_ HSYNC	LCD_ VSYNC	EVEN TOUT
	PA5	-	TIM2_ CH1/TIM2_ ETR	-	TIM8_ CH1N	-	SPI1_ SCK	-	-	-	-	OTG_HS_ ULPI_CK	-	-	-	-	EVEN TOUT
	PA6	-	TIM1_ BKIN	TIM3_ CH1	TIM8_ BKIN	-	SPI1_ MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_ PIXCLK	LCD_G2	EVEN TOUT
	PA7	-	TIM1_ CH1N	TIM3_ CH2	TIM8_ CH1N	-	SPI1_ MOSI	-	-	-	TIM14_CH1	-	ETH_MII_ RX_DV/ ETH_RMII_ CRS_DV	-	-	-	EVEN TOUT
	PA8	MCO1	TIM1_ CH1	-	-	I2C3_ SCL	-	-	USART1_ CK	-	-	OTG_FS_ SOF	-	-	-	LCD_R6	EVEN TOUT
	PA9	-	TIM1_ CH2	-	-	I2C3_ SMBA	-	-	USART1_ TX	-	-	-	-	-	DCMI_ D0	-	EVEN TOUT
	PA10	-	TIM1_ CH3	-	-	-	-	-	USART1_ RX	-	-	OTG_FS_ ID	-	-	DCMI_ D1	-	EVEN TOUT
	PA11	-	TIM1_ CH4	-	-	-	-	-	USART1_ CTS	-	CAN1_RX	OTG_FS_ DM	-	-	-	LCD_R4	EVEN TOUT
	PA12	-	TIM1_ ETR	-	-	-	-	-	USART1_ RTS	-	CAN1_TX	OTG_FS_ DP	-	-	-	LCD_R5	EVEN TOUT

6.1.7 Current consumption measurement

Figure 23. Current consumption measurement scheme



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 14: Voltage characteristics](#), [Table 15: Current characteristics](#), and [Table 16: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard, extended mission profiles are available on demand.

Table 14. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD}-V_{SS}$	External main supply voltage (including V_{DDA} , V_{DD} and V_{BAT}) ⁽¹⁾	- 0.3	4.0	V
V_{IN}	Input voltage on FT pins ⁽²⁾	$V_{SS} - 0.3$	$V_{DD} + 4.0$	
	Input voltage on TTa pins	$V_{SS} - 0.3$	4.0	
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	
	Input voltage on BOOT0 pin	V_{SS}	9.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx}-V_{SS} $	Variations between all the different ground pins including V_{REF-}	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 6.3.15: Absolute maximum ratings (electrical sensitivity)		

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum value must always be respected. Refer to [Table 15](#) for the values of the maximum allowed injected current.

6.3.9 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the [Table 56: I/O static characteristics](#). However, the recommended clock input waveform is shown in [Figure 27](#).

The characteristics given in [Table 37](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 17](#).

Table 37. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency ⁽¹⁾		1	-	50	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time ⁽¹⁾		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time ⁽¹⁾		-	-	10	
$C_{in(HSE)}$	OSC_IN input capacitance ⁽¹⁾		-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	± 1	μA

1. Guaranteed by design.

Table 44. PLLI2S (audio PLL) characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLLI2S)}^{(4)}$	PLLI2S power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLI2S)}^{(4)}$	PLLI2S power consumption on V_{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

Table 45. PLLSAI (audio and LCD-TFT PLL) characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLLSAI_IN}	PLLSAI input clock ⁽¹⁾		0.95 ⁽²⁾	1	2.10	MHz
f_{PLLSAI_OUT}	PLLSAI multiplier output clock		-	-	216	MHz
f_{VCO_OUT}	PLLSAI VCO output		100	-	432	MHz
t_{LOCK}	PLLSAI lock time	VCO freq = 100 MHz	75	-	200	μ s
		VCO freq = 432 MHz	100	-	300	
Jitter ⁽³⁾	Main SAI clock jitter	Cycle to cycle at 12.288 MHz on 48KHz period, N=432, R=5	RMS	-	90	-
			peak to peak	-	± 280	ps
		Average frequency of 12.288 MHz N = 432, R = 5 on 1000 samples	-	90	-	ps
	FS clock jitter	Cycle to cycle at 48 KHz on 1000 samples	-	400	-	ps
$I_{DD(PLLSAI)}^{(4)}$	PLLSAI power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLSAI)}^{(4)}$	PLLSAI power consumption on V_{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

Figure 33 and Figure 34 show the main PLL output clock waveforms in center spread and down spread modes, where:

F_0 is $f_{\text{PLL_OUT}}$ nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 33. PLL output clock waveforms in center spread mode

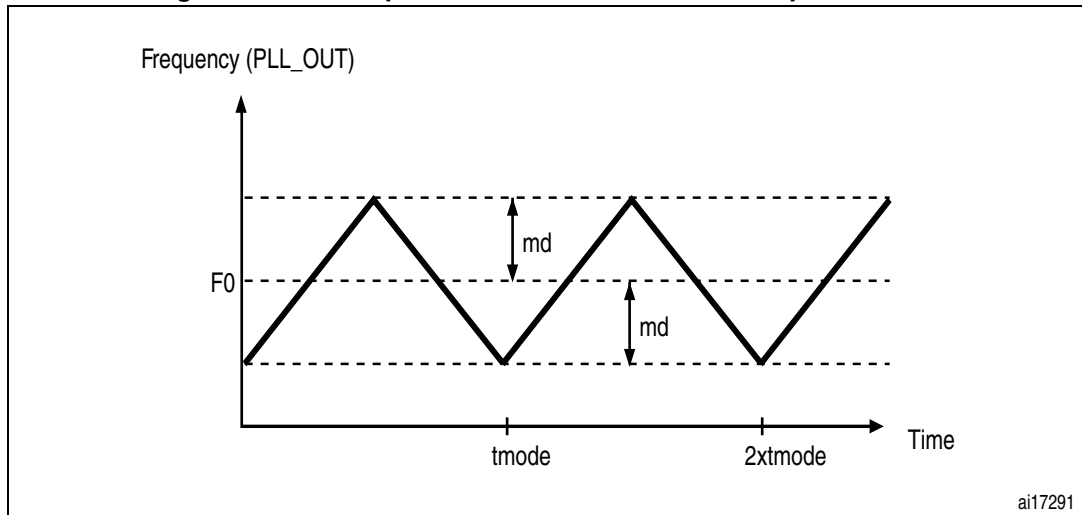


Figure 34. PLL output clock waveforms in down spread mode

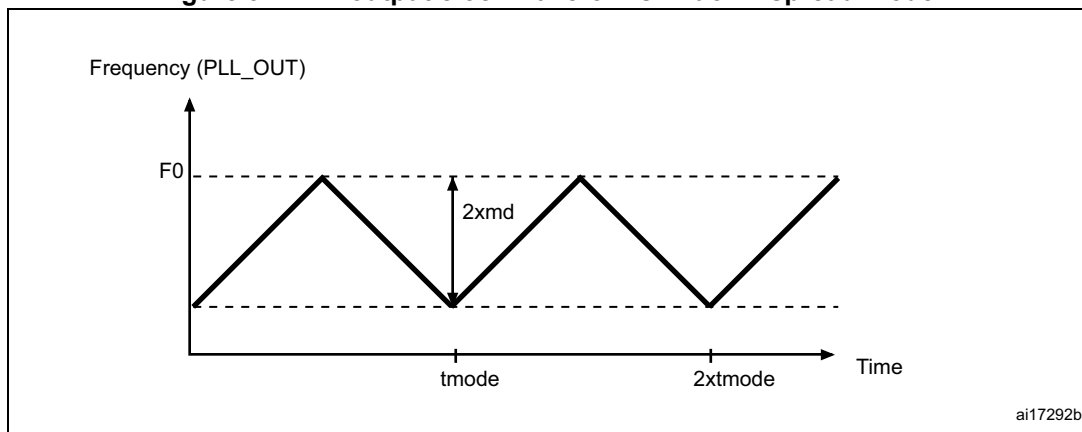
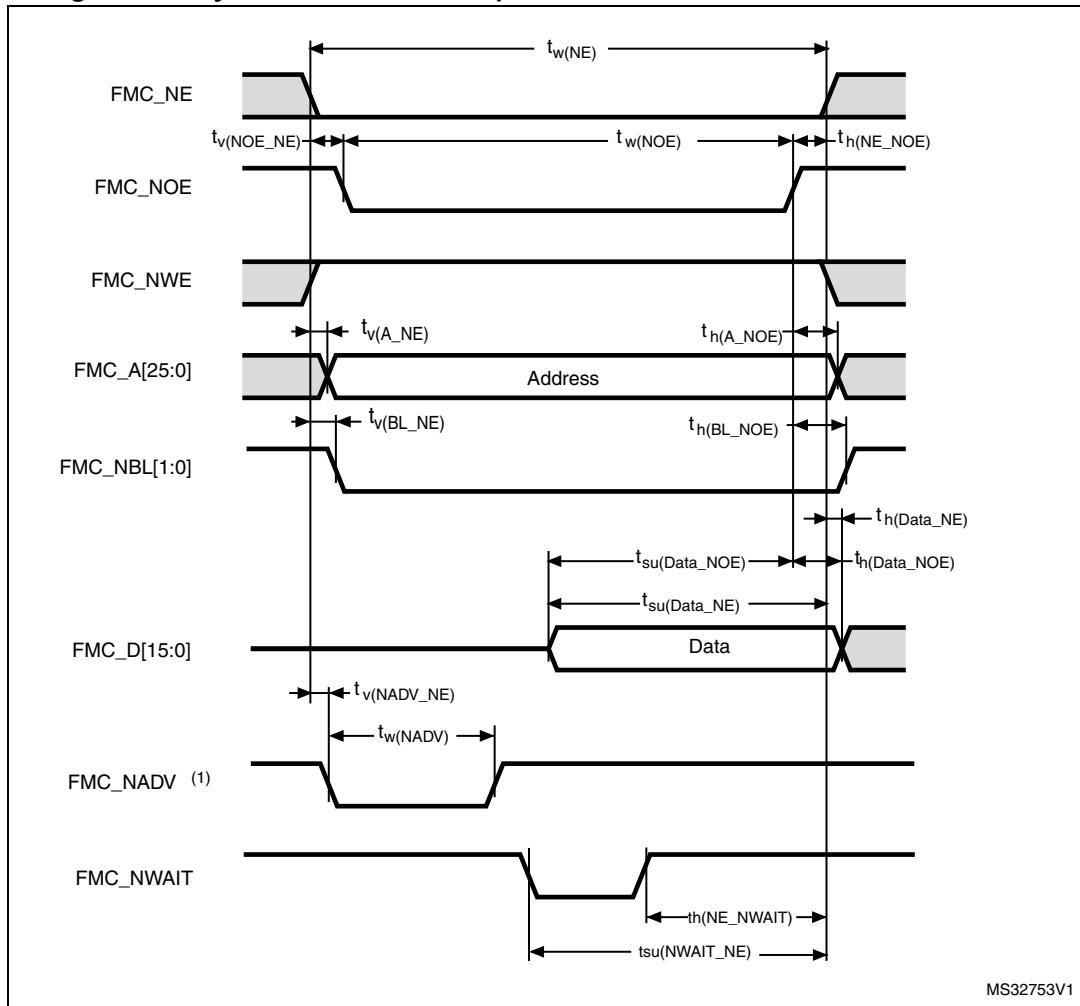


Figure 55. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

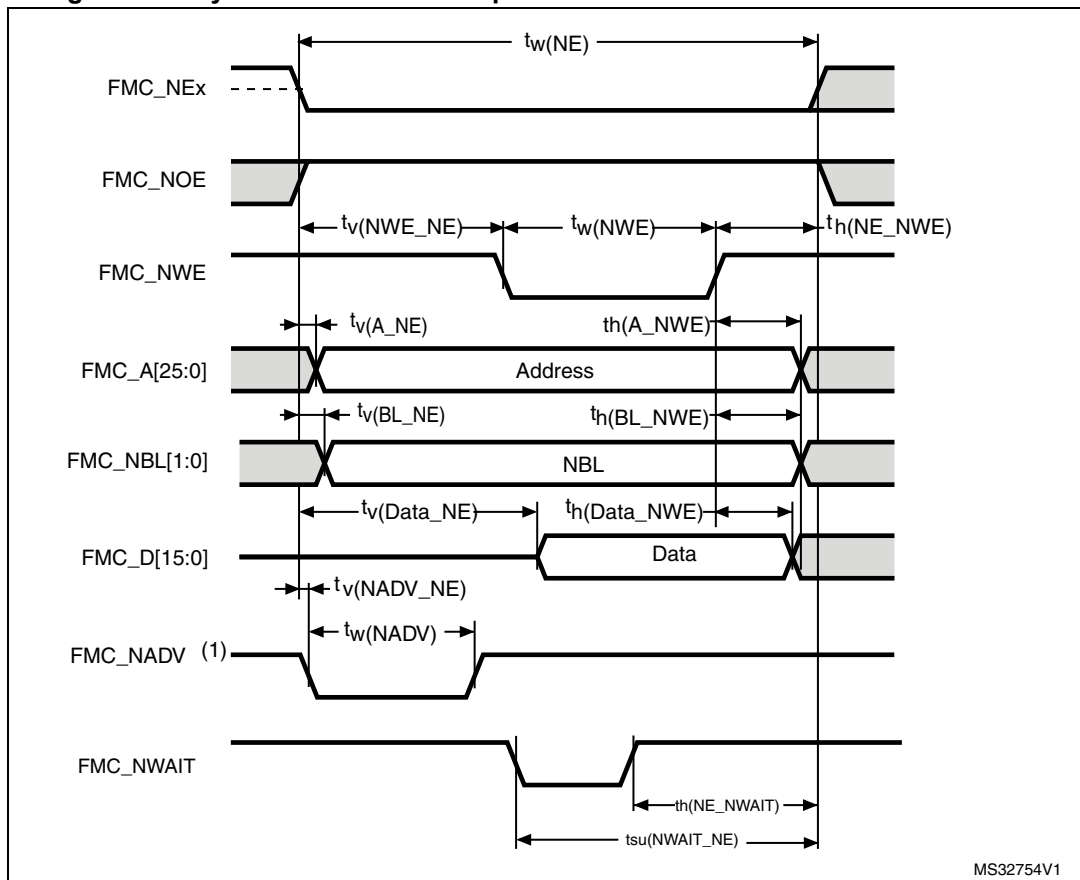


MS32753V1

1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 86. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$2T_{HCLK} - 0.5$	$2T_{HCLK} + 0.5$	ns
$t_{v(NOE_NE)}$	FMC_NEx low to FMC_NOE low	0	1	ns
$t_{w(NOE)}$	FMC_NOE low time	$2T_{HCLK}$	$2T_{HCLK} + 0.5$	ns
$t_{h(NE_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_{h(A_NOE)}$	Address hold time after FMC_NOE high	0	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_NBL valid	-	2	ns
$t_{h(BL_NOE)}$	FMC_NBL hold time after FMC_NOE high	0	-	ns
$t_{su(Data_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK} + 2.5$	-	ns
$t_{su(Data_NOE)}$	Data to FMC_NOEx high setup time	$T_{HCLK} + 2$	-	ns

Figure 56. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

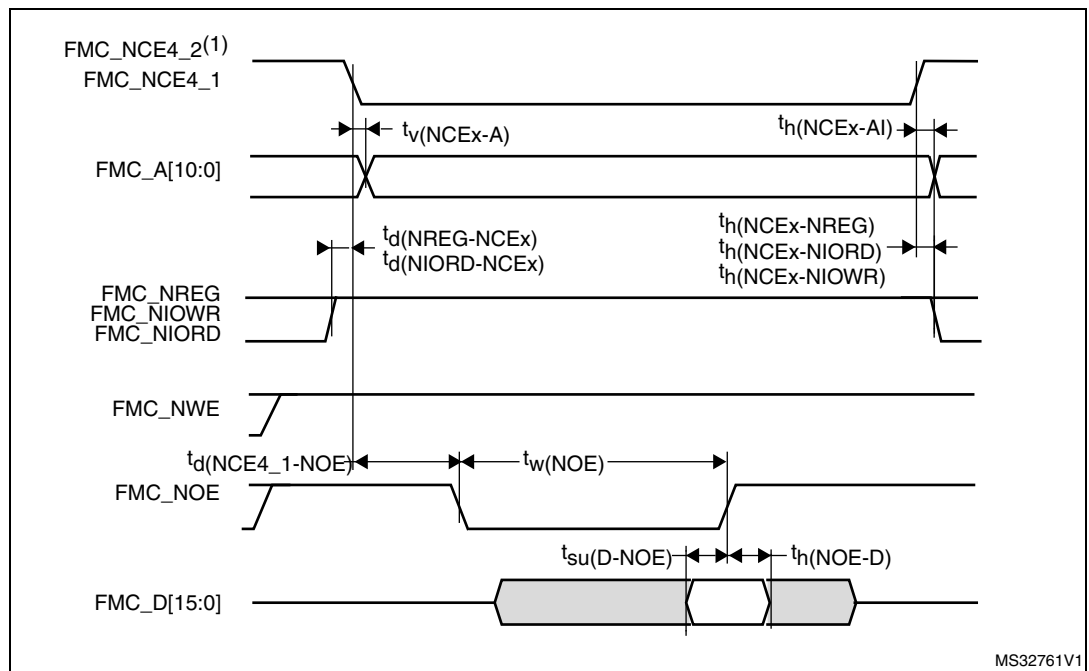
1. Mode 2/B, C and D only. In Mode 1, FMC_NADV is not used.

Table 88. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}$	$3T_{HCLK}+1$	ns
$t_{v(NWE_NE)}$	FMC_NEx low to FMC_NWE low	$T_{HCLK} - 0.5$	$T_{HCLK}+0.5$	ns
$t_{w(NWE)}$	FMC_NWE low time	T_{HCLK}	$T_{HCLK}+0.5$	ns
$t_{h(NE_NWE)}$	FMC_NWE high to FMC_NE high hold time	$T_{HCLK}+1.5$	-	ns
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	0	ns
$t_{h(A_NWE)}$	Address hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	1.5	ns
$t_{h(BL_NWE)}$	FMC_BL hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(Data_NE)}$	Data to FMC_NEx low to Data valid	-	$T_{HCLK}+2$	ns
$t_{h(Data_NWE)}$	Data hold time after FMC_NWE high	$T_{HCLK}+0.5$	-	ns
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	-	0.5	ns
$t_{w(NADV)}$	FMC_NADV low time	-	$T_{HCLK}+0.5$	ns

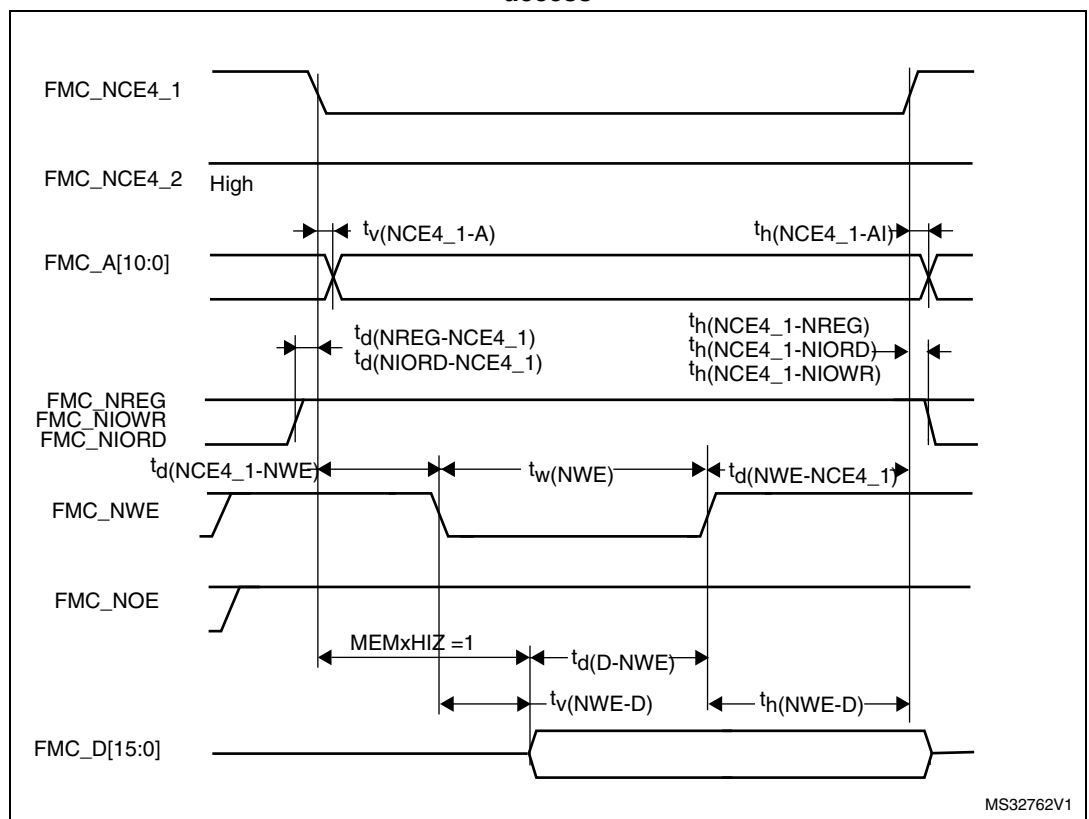
1. $C_L = 30$ pF.

2. Guaranteed by characterization results.

Figure 63. PC Card/CompactFlash controller waveforms for common memory read access

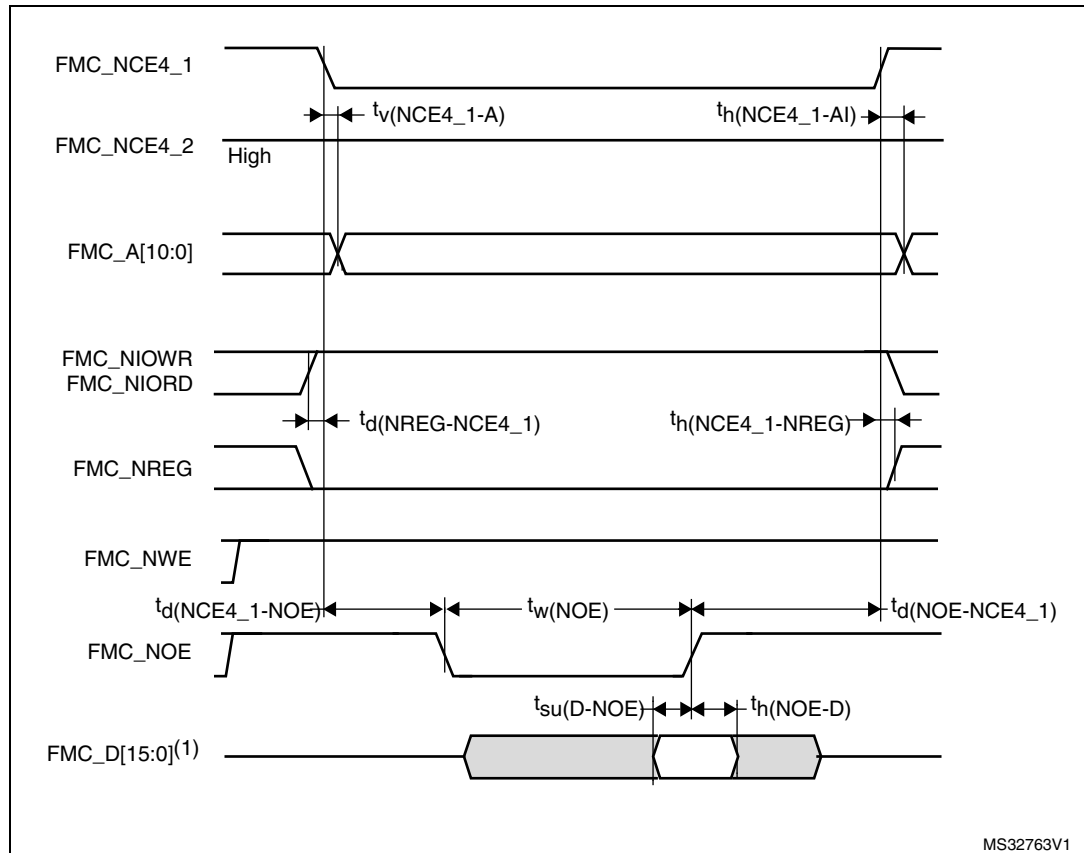
MS32761V1

1. FMC_NCE4_2 remains high (inactive during 8-bit access).

Figure 64. PC Card/CompactFlash controller waveforms for common memory write access

MS32762V1

Figure 65. PC Card/CompactFlash controller waveforms for attribute memory read access



1. Only data bits 0...7 are read (bits 8...15 are disregarded).

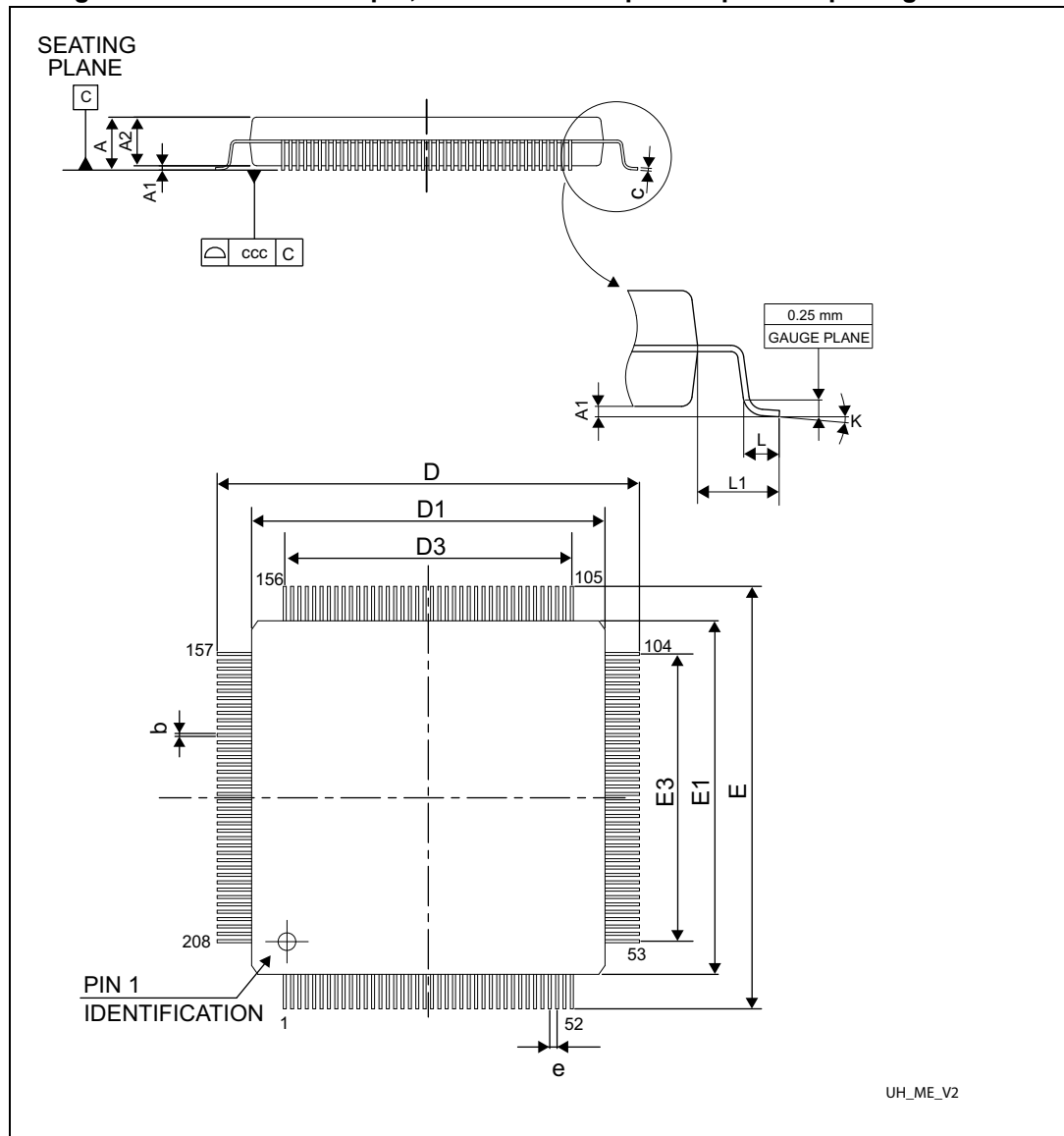
Table 110. LQPF100 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.5 LQFP208 package information

Figure 92. LQFP208 - 208-pin, 28 x 28 mm low-profile quad flat package outline



1. Drawing is not to scale.

Technical drawing of a square plate with dimensions and labels. The plate is square with a side length of 30.7. The drawing includes a central crosshair and a circular hole in the upper-left quadrant. Dimensions are provided for the plate's overall size, the hole's position, and the thickness of the plate. Labels include 208, 157, 156, 1.25, 0.3, 0.5, 1, 52, 53, 25.8, 104, 105, and 1.2.

UH_FP_V2

7.8 TFBGA216 package information

Figure 101. TFBGA216 - 216 ball 13 × 13 mm 0.8 mm pitch thin fine pitch ball grid array package outline

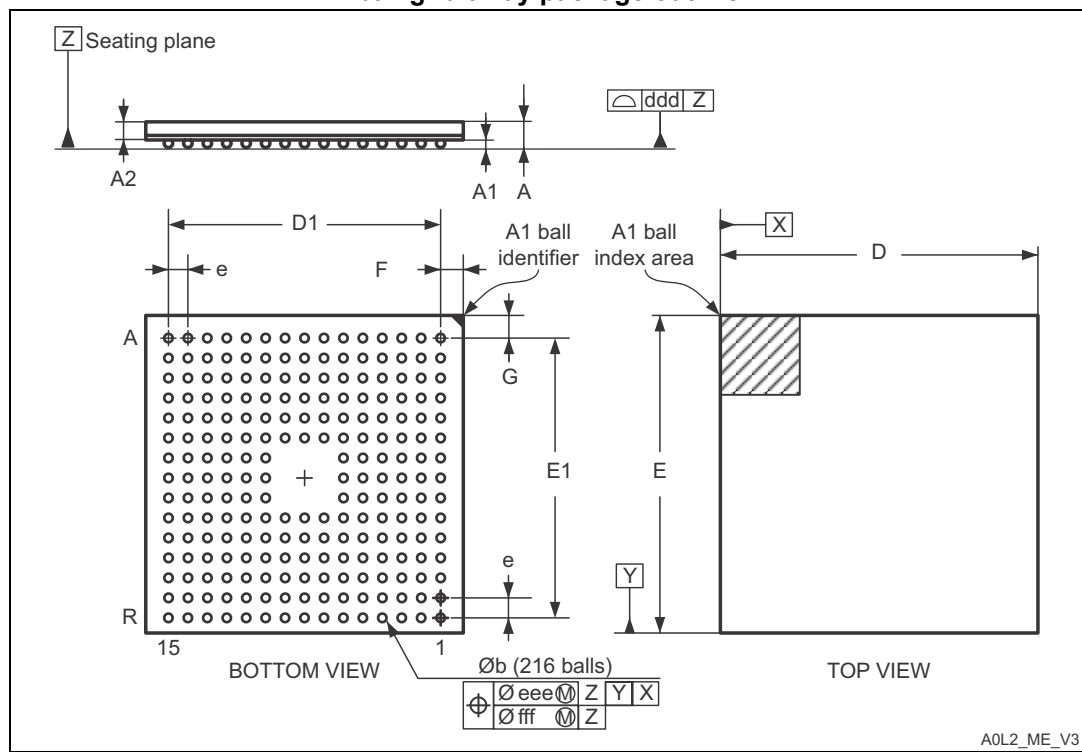


Table 120. TFBGA216 - 216 ball 13 × 13 mm 0.8 mm pitch thin fine pitch ball grid array package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.100	-	-	0.0433
A1	0.150	-	-	0.0059	-	-
A2	-	0.760	-	-	0.0299	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	12.850	13.000	13.150	0.5118	0.5118	0.5177
D1	-	11.200	-	-	0.4409	-
E	12.850	13.000	13.150	0.5118	0.5118	0.5177
E1	-	11.200	-	-	0.4409	-
e	-	0.800	-	-	0.0315	-
F	-	0.900	-	-	0.0354	-
ddd	-	-	0.100	-	-	0.0039

7.9 Thermal characteristics

The maximum chip-junction temperature, $T_J \text{ max}$, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- $T_A \text{ max}$ is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D \text{ max}$ is the sum of $P_{INT} \text{ max}$ and $P_{I/O} \text{ max}$ ($P_D \text{ max} = P_{INT} \text{ max} + P_{I/O} \text{ max}$),
- $P_{INT} \text{ max}$ is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O} \text{ max}$ represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma (V_{DD} - V_{OH}) \times I_{OH},$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 121. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient WLCSP143	31.2	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient LQFP208 - 28 × 28 mm / 0.5 mm pitch	19	
	Thermal resistance junction-ambient UFBGA169 - 7 × 7mm / 0.5 mm pitch	52	
	Thermal resistance junction-ambient UFBGA176 - 10 × 10 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

Table 124. Document revision history

Date	Revision	Changes
17-Sep-2015	6	Updated notes related to the minimum and maximum values guaranteed by design, characterization or test in production. Updated I_{DD_STOP_UDM} in Table 27: Typical and maximum current consumptions in Stop mode. Removed note related to tests in production in Table 24: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled except prefetch) or RAM and Table 26: Typical and maximum current consumption in Sleep mode. Updated Table 41: HSI oscillator characteristics. Figure 31 renamed ACCHSI accuracy versus temperature and updated. Updated Figure 38: SPI timing diagram - slave mode and CPHA = 0. Updated Section : Ethernet characteristics. Updated Table 43: Main PLL characteristics, Table 44: PLLI2S (audio PLL) characteristics and Table 45: PLLISAI (audio and LCD-TFT PLL) characteristics. Removed note 1 in Table 75: ADC static accuracy at fADC = 18 MHz, Table 76: ADC static accuracy at fADC = 30 MHz and Table 77: ADC static accuracy at fADC = 36 MHz. Updated t_d(SDCLKL_Data) and t_h(SDCLKL_Data) in Table 104: SDRAM write timings. Added Figure 96: UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array recommended footprint and Table 117: UFBGA169 recommended PCB design rules (0.5 mm pitch BGA). Added Figure 99: UFBGA176+25-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package recommended footprint and Table 119: UFBGA176+25 recommended PCB design rules (0.65 mm pitch BGA).
30-Nov-2015	7	Updated V_{SSX} - V_{SS} in Table 14: Voltage characteristics to add V_{REF-}. Updated t_d(TXEN) and t_d(TXD) minimum value in Table 72: Dynamics characteristics: Ethernet MAC signals for RMII and Table 73: Dynamics characteristics: Ethernet MAC signals for MII. Added V_{REF-} in Table 74: ADC characteristics. Added A1 minimum and maximum values in Table 111: WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package mechanical data. Updated Figure 86: LQFP144-144-pin, 20 x 20 mm low-profile quad flat package outline. Updated Figure 98: UFBGA176+25 - ball 10 x 10 mm, 0.65 mm pitch ultra thin fine pitch ball grid array package outline and Table 118: UFBGA176+25 - ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package mechanical data. Updated Figure 101: TFBGA216 - 216 ball 13 x 13 mm 0.8 mm pitch thin fine pitch ball grid array package outline and Table 120: TFBGA216 - 216 ball 13 x 13 mm 0.8 mm pitch thin fine pitch ball grid array package mechanical data.